

FEATURES

Switching transistor)

MMBT4403 (PNP)

Marking:2T

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-600	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	VCBO	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	VCEO	$I_C = -1mA, I_B = 0$	-40		V
Emitter-base breakdown voltage	VEBO	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	ICBO	$V_{CB} = -35V, I_E = 0$		-0.1	μA
Collector cut-off current	ICEO	$V_{CE} = -35V, I_B = 0$		-0.1	μA
Emitter cut-off current	IEBO	$V_{EB} = -4V, I_C = 0$		-0.1	μA
DC current gain	hFE	$V_{CE} = -2V, I_C = -150mA$	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -150mA, I_B = -15mA$		-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -150mA, I_B = -15mA$		-0.95	V
Transition frequency	fT	$V_{CE} = -10V, I_C = -20mA$ f = 100MHz	200		MHz

MMBT4403 Typical Characteristics

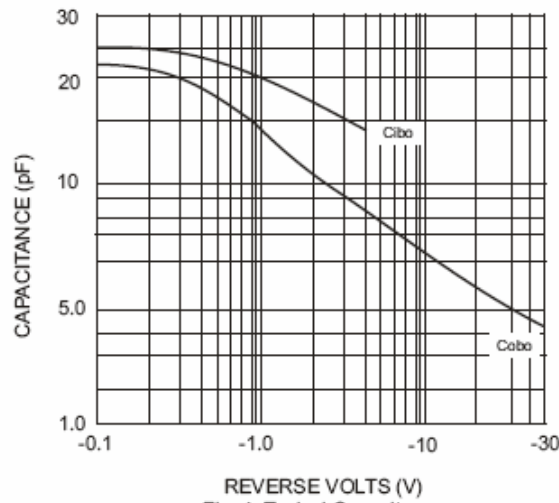


Fig. 1 Typical Capacitance

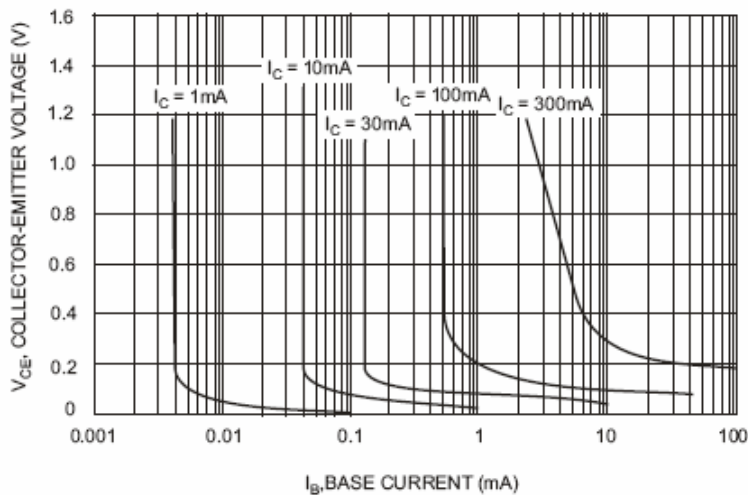


Fig. 2 Typical Collector Saturation Region

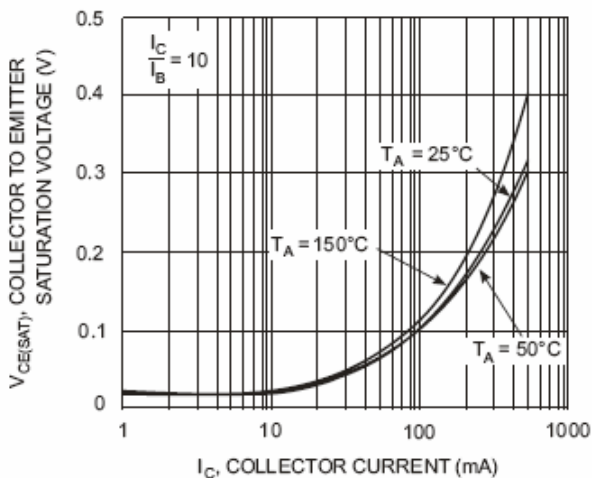


Fig. 3 Collector Emitter Saturation Voltage vs. Collector Current

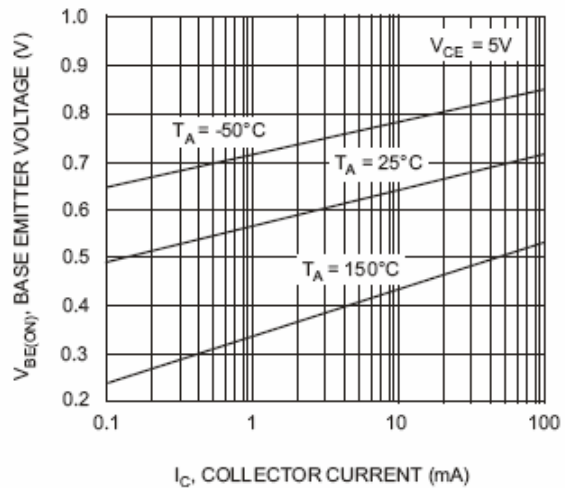


Fig. 4 Base-Emitter Voltage vs. Collector Current